

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes et al.

Title: PROGRAMMABLE MEMORY CELL USING CHARGE TRAPPING IN A GATE OXIDE

Docket No.: 303.588US3

Filed: January 22, 2004

Examiner: Tuan Nguyen



Serial No.: 10/763,136

Due Date: N/A

Group Art Unit: Unknown

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

We are transmitting herewith the following attached items (as indicated with an "X"):

☒ A return postcard.

☒ A Communication Concerning Related Applications (2 pgs.).

☒ A Supplemental Information Disclosure Statement (2 pgs.), Form 1449 (4 pgs.), and copies of 35 cited documents.

If not provided for in a separate paper filed herewith, Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional fees or credit overpayment to Deposit Account No. 19-0743.

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

Customer Number 21186

By:

Daniel J. Kluth  
Atty: Daniel J. Kluth

Reg. No. 32,146

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MEREDITH MESCHER

Name

Meredith Mescher  
Signature

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

(GENERAL)



S/N 10/763136

PATENT

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Serial No.: 10/763,136 Group Art Unit: Unknown  
Filed: January 22, 2004 Docket: 303.588US3  
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COMMUNICATION CONCERNING RELATED APPLICATION(S)

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Applicants would like to bring to the Examiner's attention the following related application(s) in the above-identified patent application:

<u>Serial/Patent No.</u>	<u>Filing Date</u>	<u>Attorney Docket</u>	<u>Title</u>
08/969,099	November	303.362US1	MEMORY USING INSULATOR TRAPS
6,232,643	13, 1997		
09/388,656	September	303.362US2	MEMORY USING INSULATOR TRAPS
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09/394,109	September	303.362US3	MEMORY USING INSULATOR TRAPS
6,140,181	10, 1999		
09/858,304	May 15,	303.362US4	MEMORY USING INSULATOR TRAPS
6,545,314	2001		
09/879,453	June 12,	303.362US5	MEMORY USING INSULATOR TRAPS
6,351,411	2001		
09/383,804	August 26,	303.588US1	MOSFET TECHNOLOGY FOR
6,521,958	1999		PROGRAMMABLE ADDRESS DECODE AND CORRECTION
09/924,659	August 8,	303.588US2	MOSFET TECHNOLOGY FOR
6,700,821	2001		PROGRAMMABLE ADDRESS DECODE AND CORRECTION
09/782,543	February	303.620US1	PROGRAMMABLE FUSE AND
6,674,667	13, 2001		ANTIFUSE AND METHOD THEREFOR
10/719,217	November	303.620US2	PROGRAMMABLE FUSE AND
	20, 2003		ANTIFUSE AND METHOD THEREFOR

COMMUNICATION CONCERNING RELATED APPLICATIONS

Serial Number: 10/763136

Filing Date: January 22, 2004

Title: PROGRAMMABLE MEMORY CELL USING CHARGE TRAPPING IN A GATE OXIDE

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Dkt: 303.588US3

Respectfully submitted,

LEONARD FORBES ET AL.

By Applicants' Representatives,

SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.

P.O. Box 2938

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Date Apr. 15, 2004 By Daniel J. Kluth  
Daniel J. Kluth  
Reg. No. 32,146

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MEREDITH MESCHER  
Name

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Signature

S/N 10/763136



PATENT

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Applicant:	Leonard Forbes et al.	Examiner:	Tuan Nguyen
Serial No.:	10/763,136	Group Art Unit:	Unknown
Filed:	January 22, 2004	Docket:	303.588US3
Title:	PROGRAMMABLE MEMORY CELL USING CHARGE TRAPPING IN A GATE OXIDE		

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**SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

In compliance with the duty imposed by 37 C.F.R. § 1.56, and in accordance with 37 C.F.R. §§ 1.97 *et. seq.*, the enclosed materials are brought to the attention of the Examiner for consideration in connection with the above-identified patent application. Applicants respectfully request that this Supplemental Information Disclosure Statement be entered and the documents listed on the attached Form 1449 be considered by the Examiner and made of record. Pursuant to the provisions of MPEP 609, Applicants request that a copy of the 1449 form, initialed as being considered by the Examiner, be returned to the Applicants with the next official communication.

Pursuant to 37 C.F.R. §1.97(b), it is believed that no fee or statement is required with the Supplemental Information Disclosure Statement. However, if an Office Action on the merits has been mailed, the Commissioner is hereby authorized to charge the required fees to Deposit Account No. 19-0743 in order to have this Supplemental Information Disclosure Statement considered.

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Serial No :10/763136

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Title: PROGRAMMABLE MEMORY CELL USING CHARGE TRAPPING IN A GATE OXIDE

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The Examiner is invited to contact the Applicants' Representative at the below-listed telephone number if there are any questions regarding this communication.

The present application is either a U.S. national patent application filed after June 30, 2003 or an international application that entered the national stage under 35 U.S.C. § 371 after June 30, 2003. Thus, Applicant believes that the U.S. Patent & Trademark Office has waived the requirement under 37 C.F.R. 1.98 (a)(2)(i) for submitting a copy of each cited U.S. patent and each U.S. patent application publication. The waiver is provided in a pre-OG notice from the U.S. Patent & Trademark Office entitled "Information Disclosure Statements May Be Filed Without Copies of U.S. Patents and Published Applications in Patent Applications filed after June 30, 2003" and dated July 11, 2003. Applicant acknowledges the requirement to submit copies of foreign patent documents and non-patent literature in accordance with 37 C.F.R. 1.98(a)(2).

Respectfully submitted,

LEONARD FORBES ET AL.

By their Representatives,

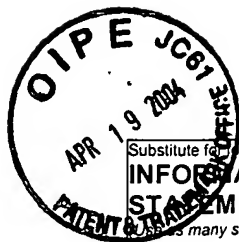
SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.  
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MEREDITH MESCHER  
Name

Meredith Mescher  
Signature



Substitute for Form 1449A/PTO  
**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**  
(Use as many sheets as necessary)

Complete if Known

Application Number	10/763136
Filing Date	January 22, 2004
First Named Inventor	Forbes, Leonard
Group Art Unit	Unknown
Examiner Name	Nguyen, Tuan

Sheet 1 of 4

Attorney Docket No: 303.588US3

### US PATENT DOCUMENTS

Examiner Initial *	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
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	US-2003/0235077 A1	12/25/2003	Forbes, L.	365	185.05	06/21/2002
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### FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T <sup>2</sup>
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### OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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EXAMINER

DATE CONSIDERED

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# **INFORMATION DISCLOSURE STATEMENT BY APPLICANT**

(Use as many sheets as necessary)

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<b>Filing Date</b>	January 22, 2004
<b>First Named Inventor</b>	Forbes, Leonard
<b>Group Art Unit</b>	Unknown
<b>Examiner Name</b>	Nguyen, Tuan

Sheet 2 of 4

Attorney Docket No: 303.588US3

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Substitute Disclosure Statement Form (PTO-1449)

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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

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Complete if Known

<b>Application Number</b>	10/763136
<b>Filing Date</b>	January 22, 2004
<b>First Named Inventor</b>	Forbes, Leonard
<b>Group Art Unit</b>	Unknown
<b>Examiner Name</b>	Nguyen, Tuan

Sheet 3 of 4

Attorney Docket No: 303.588US3

**OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
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Sheet 4 of 4

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		319	
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